

iscN-Channel MOSFET Transistor

TK8A65W, ITK8A65W

• FEATURES

- Low drain-source on-resistance: $R_{DS(ON)} = 0.53\Omega$ (typ.)
- Enhancement mode: $V_{th} = 2.5$ to $3.5V$ ($V_{DS} = 10V, I_D = 0.3mA$)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

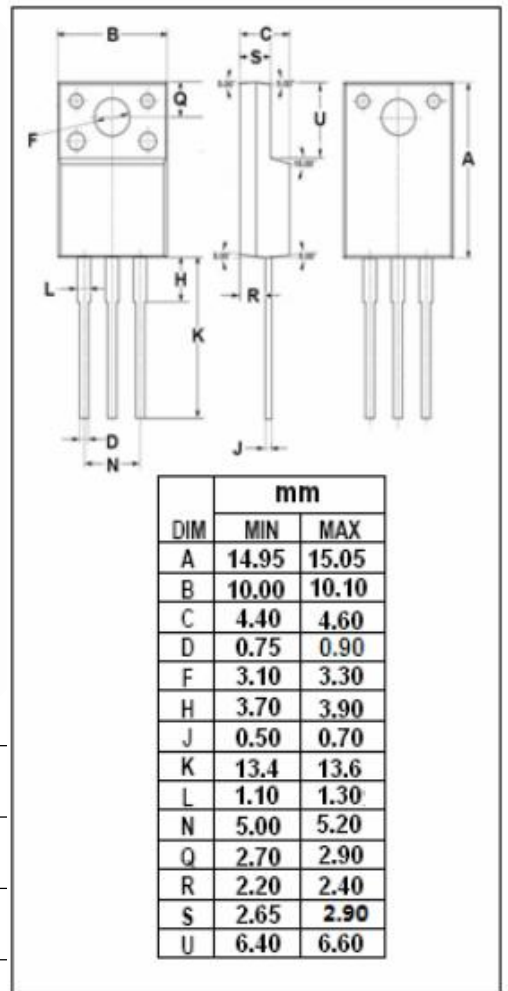
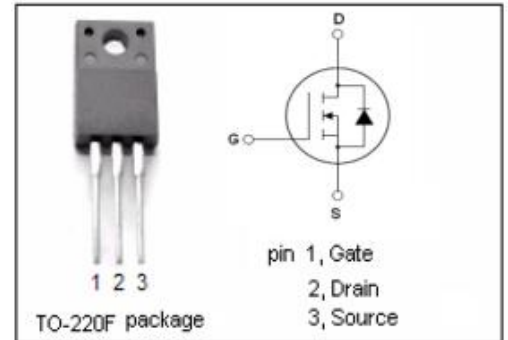
- Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous	7.8	A
I_{DM}	Drain Current-Single Pulsed	31.2	A
P_D	Total Dissipation @ $T_c = 25^\circ C$	30	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	4.17	$^\circ C/W$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62.5	$^\circ C/W$



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 10mA	650			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = 10V; I _D =0.3mA	2.5		3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =3.9A		530	650	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0V			±1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 650V; V _{GS} = 0V			10	μA
V _{SDF}	Diode forward voltage	I _{DR} =7.8A, V _{GS} = 0 V			1.7	V